

MITSUBISHI THYRISTOR MODULES

TM130RZ/EZ/GZ-24,-2H

HIGH VOLTAGE HIGH POWER GENERAL USE
INSULATED TYPE

TM130RZ/EZ/GZ-24,-2H



(RZ Type)

- **IT (AV)** Average on-state current **130A**
- **IF (AV)** Average forward current **130A**
- **VRRM** Repetitive peak reverse voltage
..... **1200/1600V**
- **VDRM** Repetitive peak off-state voltage
..... **1200/1600V**
- **MIX DOUBLE ARMS**
- **Insulated Type**
- **UL Recognized**

Yellow Card No. E80276 (N)

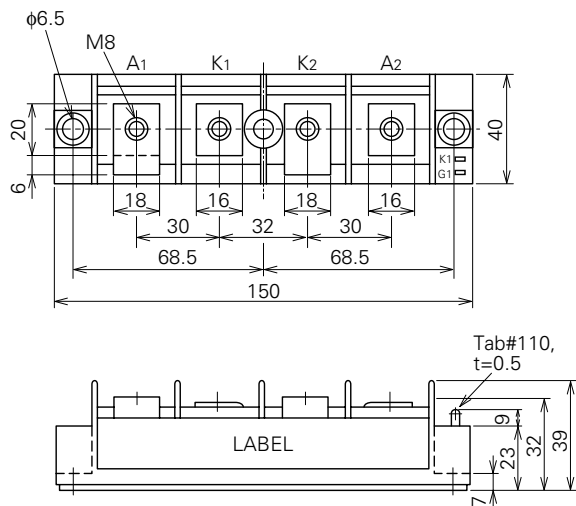
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APPLICATION

DC motor control, NC equipment, AC motor control, contactless switches,
electric furnace temperature control, light dimmers

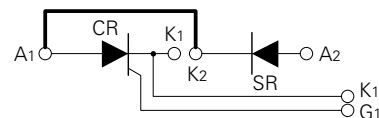
OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm

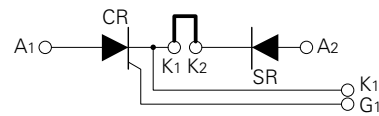


(RZ Type)

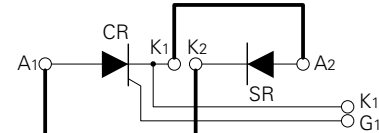
(RZ)



(EZ)



(GZ)



(Bold line is connective bar.)

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ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Voltage class		Unit
		24	2H	
VRRM	Repetitive peak reverse voltage	1200	1600	V
VRSM	Non-repetitive peak reverse voltage	1350	1700	V
VR (DC)	DC reverse voltage	960	1280	V
VDRM	Repetitive peak off-state voltage	1200	1600	V
VDSM	Non-repetitive peak off-state voltage	1350	1700	V
VD (DC)	DC off-state voltage	960	1280	V

Symbol	Parameter	Conditions	Ratings	Unit
IT (RMS), IF (RMS)	RMS current		205	A
IT (AV), IF (AV)	Average current	Single-phase, half-wave 180° conduction, Tc=78°C	130	A
ITSM, IFSM	Surge (non-repetitive) current	One half cycle at 60Hz, peak value	2600	A
I ² t	I ² t for fusing	Value for one cycle of surge current	2.8 × 10 ⁴	A ² s
di/dt	Critical rate of rise of on-state current	V _D =1/2V _{DRM} , I _G =1.0A, T _j =125°C	100	A/μs
PGM	Peak gate power dissipation		10	W
PG (AV)	Average gate power dissipation		3.0	W
VFGM	Peak gate forward voltage		10	V
VRGM	Peak gate reverse voltage		5.0	V
IFGM	Peak gate forward current		4.0	A
T _j	Junction temperature		-40~125	°C
T _{stg}	Storage temperature		-40~125	°C
V _{iso}	Isolation voltage	Charged part to case	2500	V
—	Mounting torque	Main terminal screw M8	8.83~10.8	N·m
			90~110	kg·cm
		Mounting screw M6	1.96~3.92	N·m
			20~40	kg·cm
—	Weight	Typical value	300	g

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IRRM	Repetitive peak reverse current	T _j =125°C, VRRM applied	—	—	30	mA
IDRM	Repetitive peak off-state current	T _j =125°C, VDRM applied	—	—	30	mA
VTM, VFM	Forward voltage	T _j =125°C, I _{TM} =I _{FM} =390A, instantaneous meas.	—	—	1.5	V
dv/dt	Critical rate of rise of off-state voltage	T _j =125°C, V _D =2/3V _{DRM}	500	—	—	V/μs
VGT	Gate trigger voltage	T _j =25°C, V _D =6V, R _L =2Ω	—	—	3.0	V
VGD	Gate non-trigger voltage	T _j =125°C, V _D =1/2V _{DRM}	0.25	—	—	V
IGT	Gate trigger current	T _j =25°C, V _D =6V, R _L =2Ω	15	—	100	mA
R _{th} (j-c)	Thermal resistance	Junction to case (per 1/2 module)	—	—	0.22	°C/W
R _{th} (c-f)	Contact thermal resistance	Case to fin, conductive grease applied (per 1/2 module)	—	—	0.1	°C/W
—	Insulation resistance	Measured with a 500V megohmmeter between main terminal and case	10	—	—	MΩ

Note: Items of the above table applies to the Thyristor part and the Diode part as circled in the following tables.

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MAXIMUM RATINGS

Item	VRRM	VRSM	VR (DC)	VDRM	VDSM	VD (DC)	IT (RMS)	IT (AV)	ITSM	i^2t	di/dt
							IF (RMS)	IF (AV)	IFSM		
Thyristor	○	○	○	○	○	○	○	○	○	○	○
Diode	○	○	○	—	—	—	○	○	○	○	—

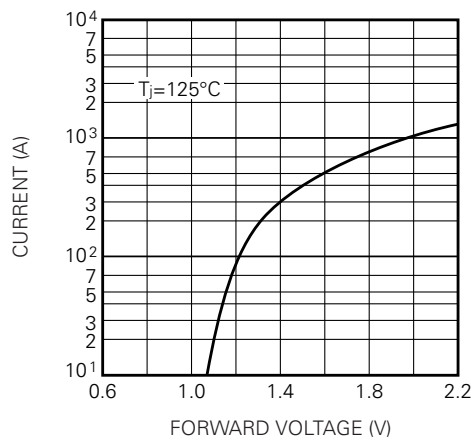
Item	PGM	PG (AV)	VFGM	IFGM	T _j	T _{stg}
Thyristor	○	○	○	○	○	○
Diode	—	—	—	—	○	○

ELECTRICAL CHARACTERISTICS

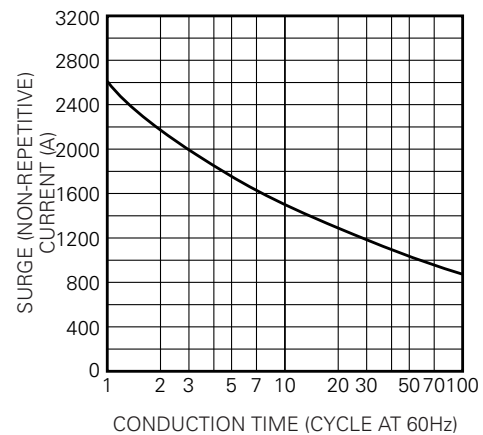
Item	IRRM	IDRM	V _{TM} V _{FM}	dv/dt	VGT	VGD	IGT	R _{th} (j-c)	R _{th} (c-f)
Thyristor	○	○	○	○	○	○	○	○	○
Diode	○	—	○	—	—	—	—	○	○

PERFORMANCE CURVES

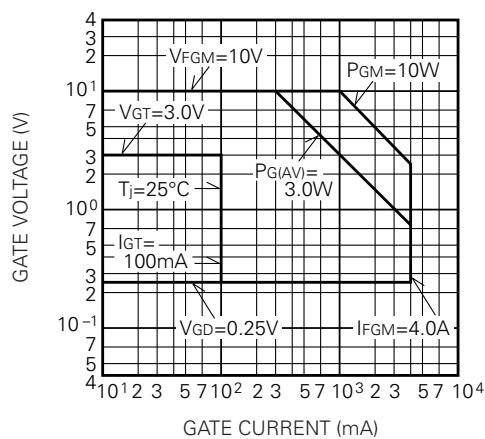
MAXIMUM FORWARD CHARACTERISTIC



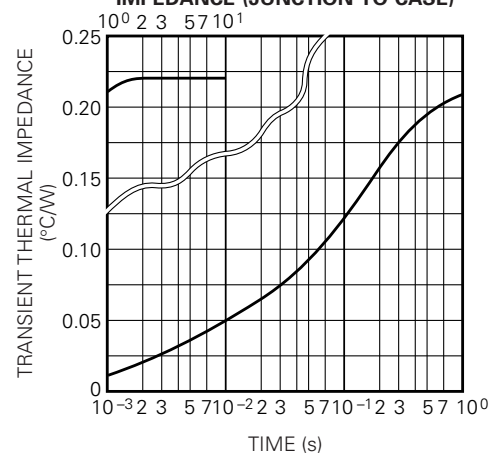
RATED SURGE (NON-REPETITIVE) CURRENT



GATE CHARACTERISTICS



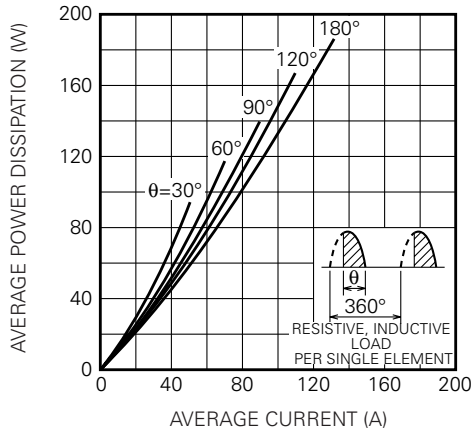
MAXIMUM TRANSIENT THERMAL IMPEDANCE (JUNCTION TO CASE)



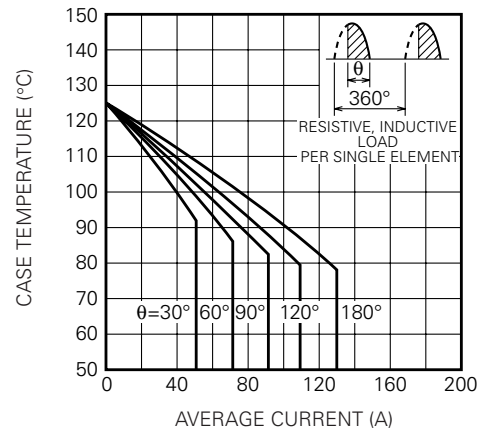
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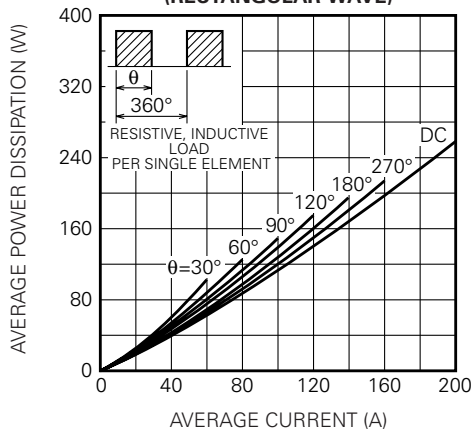
MAXIMUM AVERAGE POWER DISSIPATION (SINGLE PHASE HALFWAVE)



LIMITING VALUE OF THE AVERAGE CURRENT (SINGLE PHASE HALFWAVE)



MAXIMUM AVERAGE POWER DISSIPATION (RECTANGULAR WAVE)



LIMITING VALUE OF THE AVERAGE CURRENT (RECTANGULAR WAVE)

